



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit: 2829  
Examiner: Dana Farahani  
Confirmation no.: 5973

In Re PATENT APPLICATION Of:

Applicant: Noriyuki Miura )  
Serial No.: 10/690,579 )  
Filed: October 23, 2003 ) AMENDMENT  
For: SEMICONDUCTOR DEVICE AND )  
METAL-OXIDE SEMICONDUCTOR )  
FIELD-EFFECT TRANSISTOR )  
Attny Ref.: MAE 296 )

May 24, 2005

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

This paper is in response to the Official Action mailed on February 24, 2005. No fee is due. However, please charge our Deposit Account No. 18-0002 if any fees are needed to enter this paper, and please advise us accordingly. It is noted that no petition is required because of the authorization to charge, but please consider this paper a petition for extension of time if needed.

Claims 1 and 9 are amended to recite that "conductivity types of the channel region, the source and the drain are all N-type." This is discussed below.

**FEE ENCLOSED: \$ 0**  
**Please charge any further**  
**fee to our Deposit Account**  
**No. 18-0002**